

DIAMFAB

Diamond epitaxial layer for power device application



Gauthier Chicot (Projet Leader), David Eon (Project Initiator), Julien Pernot (Scientific Expert) and Etienne Gheeraert (Scientific Expert).

DiamFab is a future company currently in incubation step before foundation in 2019. This original idea came from a small group of persons at Institut Néel who is participating to DiamFab. The research work performed for 20 years allows the company to acquire many skills and know-how on homoepitaxial growth of diamond and doping. During the pre-incubation, Linksium is an incubator company helping inventors to build their projects and prepare company assembly. DiamFab business model is focused



on diamond epitaxial growth and development of diamond power devices components.

Diamond is the next generation semiconductor material for high power electronic applications with its unique electrical and thermal properties. Based on its expertise in diamond epitaxy, DiamFab produces bare die device ready diamond. On a well selected substrate, the desired layers of p-type diamond are grown by Plasma enhanced CVD with a wide range of doping level and thickness. The epitaxial layer fabricated by DiamFab is the key part of the electronic component and its properties (crystalline quality, thickness and doping level) directly determine the performances of devices fabricated with it. DiamFab material is electronic grade and is ready for electronic devices fabrication but can also be used for other applications such as optical ones.

http://diamfab.eu/